

Power transistor

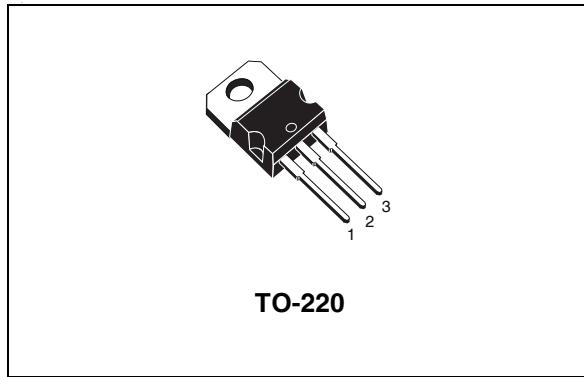
Applications

- Linear and switching industrial equipment

Description

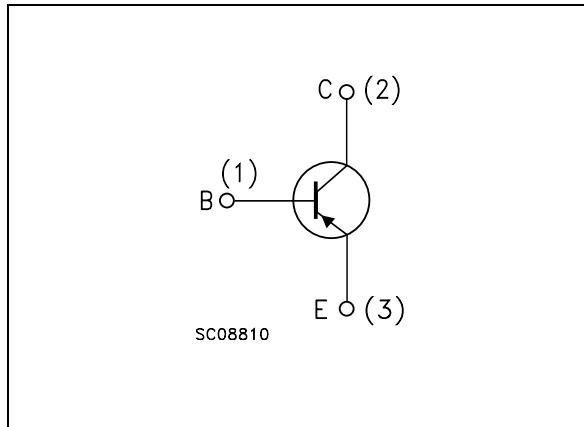
The TIP32C is a silicon Epitaxial-base PNP power transistor in Jedec TO-220 plastic package. It is intended for use in medium power linear and switching applications.

The complementary NPN type is TIP31C.



TO-220

Internal schematic diagram



Order codes

Part number	Marking	Package	Packing
TIP32C	TIP32C	TO-220	Tube

1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	-100	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-100	V
V_{EBO}	Emitte-base voltage ($I_C = 0$)	-5	V
I_C	Collector current	-3	A
I_{CM}	Collector peak current ($t_P < 5\text{ms}$)	-5	A
I_B	Base current	-1	A
P_{TOT}	Total dissipation at $T_{case} = 25^\circ\text{C}$ $T_{amb} = 25^\circ\text{C}$	40 2	W W
T_{stg}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_J	Max. operating junction temperature	150	$^\circ\text{C}$

2 Electrical characteristics

($T_{case} = 25^\circ\text{C}$; unless otherwise specified)

Table 2. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector cut-off current ($I_B = 0$)	$V_{CB} = -60\text{V}$			-0.3	mA
I_{CES}	Collector cut-off current ($V_{BE} = 0$)	$V_{CB} = -100\text{V}$			-0.2	mA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = -5\text{V}$			-1	mA
$V_{CEO(sus)}^{(1)}$	Collector-emitter sustaining voltage ($I_B = 0$)	$I_C = -30\text{mA}$	-100			V
$V_{CE(sat)}^{(1)}$	Collector-emitter saturation voltage	$I_C = -3\text{A}$ $I_B = 375\text{mA}$			-1.2	V
$V_{BE(on)}^{(1)}$	Base-emitter voltage	$I_C = -3\text{A}$ $V_{CE} = -4\text{V}$			-1.8	V
$h_{FE}^{(1)}$	DC current gain	$I_C = -1\text{A}$ $V_{CE} = -4\text{V}$ $I_C = -3\text{A}$ $V_{CE} = -4\text{V}$	25 10		50	

1. Pulsed duration = 300 ms, duty cycle $\geq 1.5\%$.